MOSFET - Power for 1-Cell Lithium-ion Battery Protection



This power MOSFET features a low on-state resistance. This device is suitable for applications such as power switches of portable machines. Best suited for 1-cell lithium-ion battery applications.

Features

- 2.5 V drive
- Common–Drain type
- ESD Diode-Protected Gate
- Pb-Free, Halogen Free and RoHS Compliance

Typical Applications

• 1-Cell Lithium-ion Battery Charging and Discharging Switch

SPECIFICATIONS

ABSOLUTE MAXIMUM RATINGS at $T_A = 25$ °C

Parameter	Symbol	Value	Unit
Source to Source Voltage	V _{SSS}	12	V
Gate to Source Voltage	V_{GSS}	±8	V
Source Current (DC)	Is	40	Α
Source Current (Pulse) PW ≤ 10 μS, Duty Cycle ≤ 1%	I _{SP}	140	Α
Total Dissipation (Note 1)	P _T	3.3	W
Junction Temperature	TJ	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient (Note 1)	$R_{ heta JA}$	37	°C/W

1. Surface mounted on ceramic substrate (5000 $\text{mm}^2 \times 0.8 \text{ mm}$)

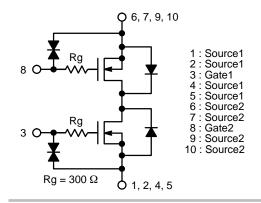


ON Semiconductor®

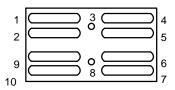
www.onsemi.com

V _{SSS}	R _{SS(ON)} MAX	I _S MAX
12 V	1.8 mΩ @ 4.5 V	40 A
	1.9 mΩ @ 3.8 V	
	2.6 mΩ @ 3.1 V	
	4.2 mΩ @ 2.5 V	

ELECTRICAL CONNECTION N-Channel



PIN ASSIGNMENT



MARKING DIAGRAM





WLCSP10 3.54x1.77x0.140 CASE 567XB PB = Specific Device Code A = Assembly Location

Y = Year W = Work Week

ZZ = Assembly Lot

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 2 of this data sheet.

ELECTRICAL CHARACTERISTICS at T_A = 25°C

				Value			
Parameter	Symbol	Condition	ıs	Min	Тур	Max	Unit
Source to Source Breakdown Voltage	V _{(BR)SSS}	I _S = 1 mA, V _{GS} = 0 V	Test Circuit 1	12	-	-	V
Zero Gate Voltage Source Current	I _{SSS}	V _{SS} = 10 V, V _{GS} = 0 V	Test Circuit 1	-	-	1	μΑ
Gate to Source Leakage Current	I _{GSS}	$V_{GS} = \pm 8 \text{ V}, V_{SS} = 0 \text{ V}$	Test Circuit 2	-	_	±1	μΑ
Gate Threshold Voltage	V _{GS} (th)	$V_{SS} = 6 \text{ V}, I_{S} = 1 \text{ mA}$	Test Circuit 3	0.4	-	1.3	V
Static Source to Source On-State	R _{SS} (on)	$I_S = 5 \text{ A}, V_{GS} = 4.5 \text{ V}$	Test Circuit 4	0.8	1.25	1.8	mΩ
Resistance		I _S = 5 A, V _{GS} = 3.8 V	Test Circuit 4	0.85	1.35	1.9	mΩ
		I _S = 5 A, V _{GS} = 3.1 V	Test Circuit 4	1.0	1.7	2.6	mΩ
		I _S = 5 A, V _{GS} = 2.5 V	Test Circuit 4	1.2	2.1	4.2	mΩ
Turn-ON Delay Time	t _d (on)	V _{SS} = 6 V, V _{GS} = 3.8 V, I _S = 5 A,		-	25	_	μS
Rise Time	t _r	R_G = 10 kΩ Test Circuit 5	$R_G = 10 \text{ k}\Omega$ Test Circuit 5		100	-	μS
Turn-OFF Delay Time	t _d (off)			-	165	-	μS
Fall Time	t _f			-	148	-	μS
Total Gate Charge	Qg	V_{SS} = 6 V, V_{GS} = 3.8 V, I_{S} Test Circuit 6	= 5 A	-	62	-	nC
Forward Source to Source Voltage	V _{F(S-S)}	I _S = 3 A, V _{GS} = 0 V	Test Circuit 7	-	0.75	1.2	V

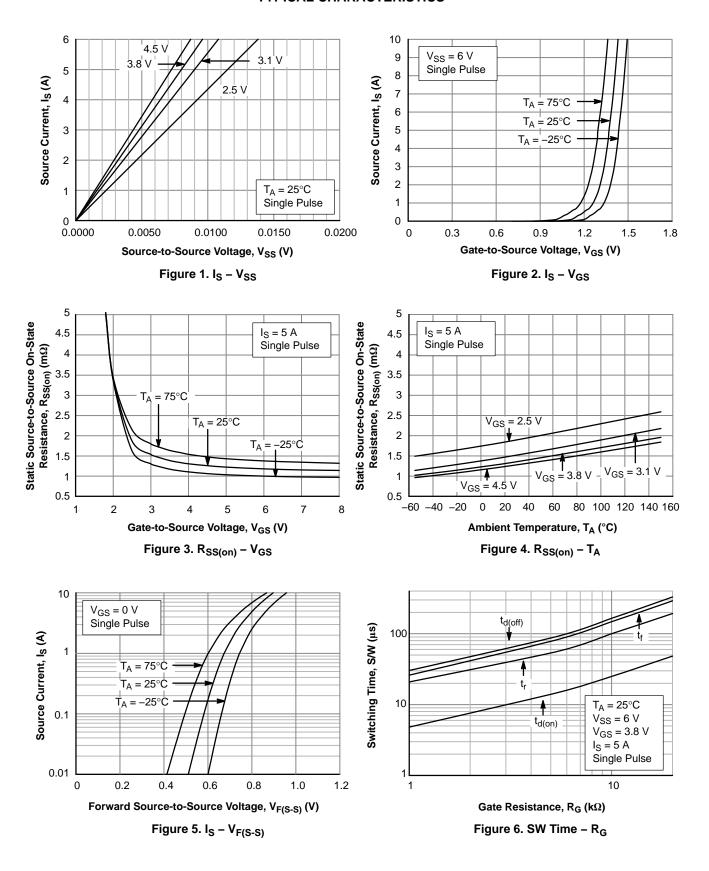
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing) [†]
EFC2K103NUZTDG	РВ	WLCSP10, 3.54 × 1.77 × 0.140 (Pb–Free / Halogen Free)	5,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS (Continued)

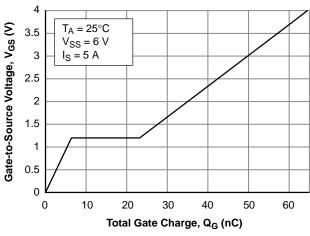


Figure 7. V_{GS} – Q_G

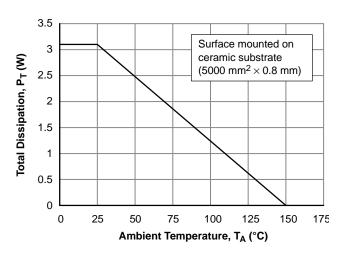


Figure 8. P_T – T_A

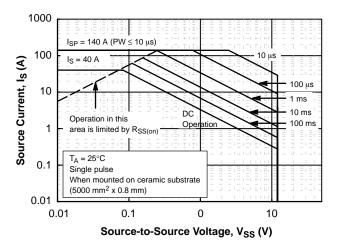


Figure 9. Safe Operating Area

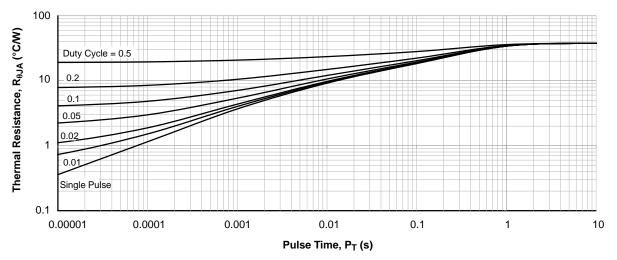


Figure 10. Thermal Response

TEST CIRCUITS ARE EXAMPLES OF MEASURING FET1 SIDE

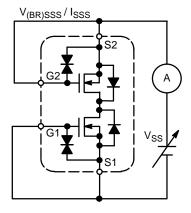
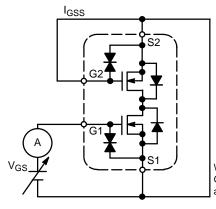


Figure 11. Test Circuit



When FET1 is measured, Gate and Source of FET2 are short–circuited.

Figure 12. Test Circuit

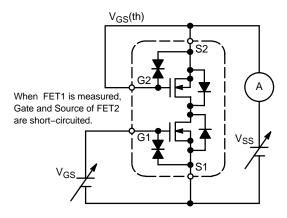


Figure 13. Test Circuit 3

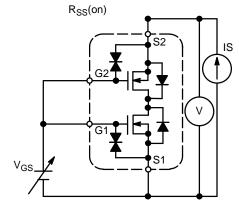


Figure 14. Test Circuit

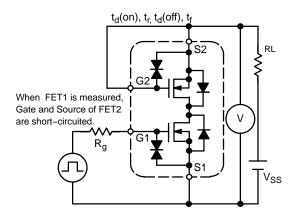


Figure 15. Test Circuit 5

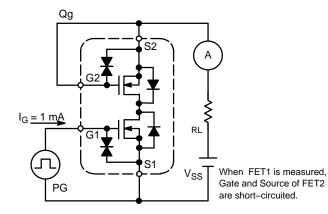


Figure 16. Test Circuit

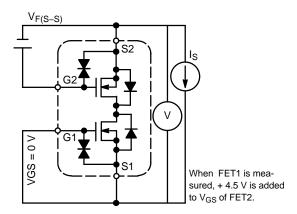


Figure 17. Test Circuit

NOTE: When FET2 is measured, the position of FET1 and FET2 is switched.

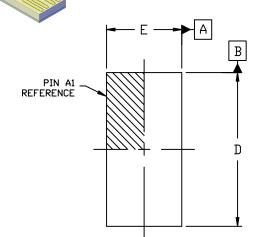
NOTE: Since the EFC2K103NUZ is a MOSFET product, please avoid using this device in the vicinity of highly charged objects. Please contact sales for use except the designated application.



WLCSP10, 3.54x1.77x0.14 CASE 567XB

ISSUE O

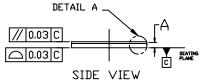
DATE 09 OCT 2018



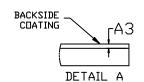
NOTES:

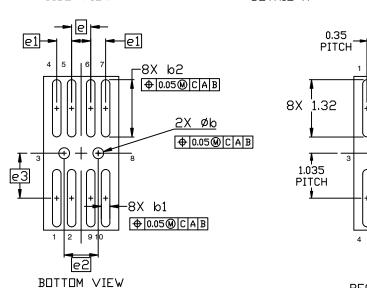
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS

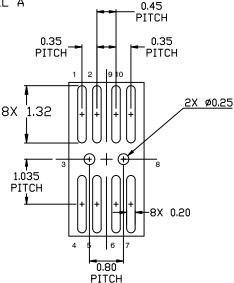
	MILLIMETERS			
DIM	MIN.	N□M.	MAX.	
Α	0.11	0.14	0.17	
A3		0.04 REF		
b	0.22	0.25 0.28		
b1	0.17	0.20	0.23	
b2	1.29	1.32	1.35	
D	3.51	3.54	3.57	
E	1.74	1.77 1.80		
e	0.45 BSC			
e1	0.35 BSC			
e2	0.80 BSC			
e3	1.035 BSC			



TOP VIEW







RECOMMENDED MOUNTING FOOTPRINT

GENERIC MARKING DIAGRAM*

XXXXX. AYWZZ=

XXXX = Specific Device Code

= Assembly Location Α = Year

= Work Week W ZZ = Assembly Lot Code = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98AON98952G	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	WLCSP10, 3.54x1.77x0.14		PAGE 1 OF 1	

onsemi and Onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves brisefin and of 160 m are trademarked to demonstrate the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales